Andrey B Krysa

List of Publications by Year
in descending order

255	2,799	218677	254184
papers	citations	26 h-index	43 g-index

256	256	256	2133
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Design and Performance of an InGaAsâ€“InP Single-Photon Avalanche Diode Detector. IEEE Journal of Quantum Electronics, 2006, 42, 397-403.	1.9	120
2	A quantum light-emitting diode for the standard telecom window around 1,550â€‰nm. Nature Communications, 2018, 9, 862.	12.8	119
3	High speed InAs electron avalanche photodiodes overcome the conventional gain-bandwidth product limit. Optics Express, 2011, 19, 23341.	3.4	95
4	Direct Measurement of the Hole-Nuclear Spin Interaction in Single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InP</mml:mi><mml:mo>/</mml:mo><mml:mi>GaInP</mml:mi></mml:math>Quantum Dots Using Photoluminescence Spectroscopy. Physical Review Letters, 2011, 106, 027402.	7.8	93
5	InGaAsâˆ•AlAsSbâˆ•InP quantum cascade lasers operating at wavelengths close to 3Î¼m. Applied Physics Letters, 2007, 90, 021108.	3.3	89
6	Tunable ultraviolet output from an intracavity frequency-doubled red vertical-external-cavity surface-emitting laser. Applied Physics Letters, 2006, 89, 061114.	3.3	83
7	Element-sensitive measurement of the holeâ€“nuclear spin interaction in quantum dots. Nature Physics, 2013, 9, 74-78.	16.7	70
8	Quantum teleportation using highly coherent emission from telecom C-band quantum dots. Npj Quantum Information, 2020, 6, .	6.7	66
9	Structural analysis of strained quantum dots using nuclear magnetic resonance. Nature Nanotechnology, 2012, 7, 646-650.	31.5	65
10	Pumping of Nuclear Spins by Optical Excitation of Spin-Forbidden Transitions in a Quantum Dot. Physical Review Letters, 2010, 104, 066804.	7.8	61
11	Î» â‰¥ 3.1 â€‰Î¼m room temperature InGaAs/AlAsSb/InP quantum cascade lasers. Applied Physics Letters, 2009, 94, .	3.3	55
12	Universal Growth Scheme for Quantum Dots with Low Fine-Structure Splitting at Various Emission Wavelengths. Physical Review Applied, 2017, 8, .	3.8	53
13	Single-mode surface-emitting quantum-cascade lasers. Applied Physics Letters, 2005, 86, 211102.	3.3	51
14	Femtosecond Alexandrite laser passively mode-locked by an InP/InGaP quantum-dot saturable absorber. Optics Letters, 2018, 43, 232.	3.3	48
15	InAs thermophotovoltaic cells with high quantum efficiency for waste heat recovery applications below 1000 Â°C. Solar Energy Materials and Solar Cells, 2018, 179, 334-338.	6.2	44
16	Temperature Dependence of Leakage Current in InAs Avalanche Photodiodes. IEEE Journal of Quantum Electronics, 2011, 47, 1123-1128.	1.9	43
17	Homogeneous Array of Nanowire-Embedded Quantum Light Emitters. Nano Letters, 2013, 13, 861-865.	9.1	40
18	InP/AlGaInP quantum dot semiconductor disk lasers for CW TEM_00 emission at 716 â€“ 755 nm. Optics Express, 2009, 17, 21782.	3.4	39

#	Article	IF	Citations
19	Linearly Polarized Emission from an Embedded Quantum Dot Using Nanowire Morphology Control. Nano Letters, 2015, 15, 1559-1563.	9.1	37
20	High peak power Î»â^¼3.3 and 3.5â€‚Î¼m InGaAs/AlAs(Sb) quantum cascade lasers operating up to 400 K. Applied Physics Letters, 2010, 97, .	3.3	35
21	Coherence in single photon emission from droplet epitaxy and Stranskiâ€“Krastanov quantum dots in the telecom C-band. Applied Physics Letters, 2021, 118, .	3.3	34
22	InP-GaInP quantum-dot lasers emitting between 690-750 nm. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1035-1040.	2.9	32
23	Fingerprints of spatial charge transfer in quantum cascade lasers. Journal of Applied Physics, 2007, 102, .	2.5	32
24	High-performance distributed feedback quantum cascade lasers grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2004, 85, 5529-5531.	3.3	31
25	Characterization of intersubband devices combining a nonequilibrium many body theory with transmission spectroscopy experiments. Journal of Materials Science: Materials in Electronics, 2007, 18, 689-694.	2.2	29
26	Dynamics of optically induced nuclear spin polarization in individual<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>InP</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Ga</mml:mtext></mml:mrow></mml:msub></mml:mrow></mml:math> dots. Physical Review B, 2010, 81, .	3.2	28
27	MBE growth and characterization of ZnTe epilayers and ZnCdTe/ZnTe structures on GaAs(100) and ZnTe(100) substrates. Journal of Crystal Growth, 2000, 214-215, 35-39.	1.5	27
28	Room-temperature operation of InGaAs/AlInAs quantum cascade lasers grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2003, 83, 1921-1922.	3.3	27
29	MOVPE-grown quantum cascade lasers operating at â^¼9Î¼m wavelength. Journal of Crystal Growth, 2004, 272, 682-685.	1.5	27
30	Overhauser effect in individualInPâ•GaxIn1â^'xPdots. Physical Review B, 2008, 77, .	3.2	27
31	Ultrafast phase-resolved pump-probe measurements on a quantum cascade laser. Applied Physics Letters, 2008, 93, 151106.	3.3	26
32	Gigahertz-Clocked Teleportation of Time-Bin Qubits with a Quantum Dot in the Telecommunication <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>C</mml:mi></mml:math> Band. Physical Review Applied, 2020, 13, .	3.8	25
33	Room-temperature operation of Î»â‰ˆ7.5Î¼m surface-plasmon quantum cascade lasers. Applied Physics Letters, 2006, 88, 181103.	3.3	24
34	Vertical subwavelength mode confinement in terahertz and mid-infrared quantum cascade lasers. Applied Physics Letters, 2011, 98, .	3.3	22
35	Intersubband spectroscopy of quantum cascade lasers under operating conditions. Applied Physics Letters, 2006, 88, 131105.	3.3	21
36	Optical properties of InPâ•GaInP quantum-dot laser structures. Applied Physics Letters, 2004, 85, 1904-1906.	3.3	20

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37	Al<inline-formula><tex-math>$_{f 0.52}$</tex-math></inline-formula>In<inline-formula><tex-math>$_{f 0.48}$</tex-math></inline-formula>P SAM-APD as a Blue-Green Detector. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 142-146.	2.9	20
38	Measurement of the electronâ€“hole pair creation energy in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" id="mml29" display="inline" overflow="scroll" altimg="si29.gif"><mml:msub><mml:mrow><mml:mi>A</mml:mi><mml:mi>l</mml:mi></mml:mrow><mml:mrow><mml:mn>0</mml:m using X-ray r. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2018, 879, 64-68.	1.6	20
39	Passive Mode-Locking of a Tiâ€‰:â€‰Sapphire Laser by InGaP Quantum-Dot Saturable Absorber. IEEE Photonics Technology Letters, 2010, 22, 209-211.	2.5	19
40	Ultrafast probing of light-matter interaction in a midinfrared quantum cascade laser. Applied Physics Letters, 2008, 93, 091105.	3.3	18
41	Al_{0.52}In_{0.48}P⁵⁵Fe x-ray-photovoltaic battery. Journal Physics D: Applied Physics, 2016, 49, 355601.	2.8	18
42	Room-temperature laser cathode-ray tube based on an ZnCdSe/ZnSe superlattice. Quantum Electronics, 1995, 25, 726-728.	1.0	17
43	InGaAsâˆ•AlAsSbâˆ•InP strain compensated quantum cascade lasers. Applied Physics Letters, 2007, 90, 151105.	3.3	17
44	Al_{0.52}In_{0.48}P avalanche photodiodes for soft X-ray spectroscopy. Journal of Instrumentation, 2016, 11, P03021-P03021.	1.2	17
45	InAsP quantum dot lasers grown by MOVPE. Optics Express, 2015, 23, 27282.	3.4	16
46	Improved performance of In0.6Ga0.4Asâˆ•AlAs0.67Sb0.33âˆ•InP quantum cascade lasers by introduction of AlAs barriers in the active regions. Applied Physics Letters, 2007, 91, 051123.	3.3	15
47	Low threshold InP/AlGaInP on GaAs QD laser emitting at âˆ¼740nm. Journal of Crystal Growth, 2007, 298, 663-666.	1.5	15
48	Temperature-Dependent Threshold Current in InP Quantum-Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1343-1348.	2.9	15
49	InP-Based Midinfrared Quantum Cascade Lasers for Wavelengths Below 4 Î¼m. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1417-1425.	2.9	15
50	InAs Photodiodes for 3.43 $mu ext{m}$ Radiation Thermometry. IEEE Sensors Journal, 2015, 15, 5555-5560.	4.7	15
51	740â€…nm InPâˆ•GaInP quantum-dot laser with 190â€…Aâ€…cmâˆ’2 room temperature threshold current density. Electronics Letters, 2005, 41, 247.	1.0	14
52	Electrooptic tuning of InP-based microphotonic Fabry-Perot filters. Journal of Lightwave Technology, 2005, 23, 2169-2174.	4.6	14
53	High performance, high temperature Î»â‰ˆ3.7â€‰Î¼m InGaAs/AlAs(Sb) quantum cascade lasers. Applied Physics Letters, 2009, 95, 111113.	3.3	14
54	Impact Ionization Coefficients in $hbox{Al}_{0.52} hbox{In}_{0.48}hbox{P}$. IEEE Electron Device Letters, 2011, 32, 1528-1530.	3.9	14

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55	Dual-wavelength InP quantum dot lasers. Applied Physics Letters, 2014, 104, .	3.3	14
56	Characterisation of Al0.52In0.48P mesa p-i-n photodiodes for X-ray photon counting spectroscopy. Journal of Applied Physics, 2016, 120, 024502.	2.5	14
57	Uniformity of radiation from a laser CRT based on a low-dimensional GaInP/AlGaInP structure with resonance-periodic gain. Quantum Electronics, 2004, 34, 919-923.	1.0	13
58	GaAs-based self-aligned laser incorporating InGaP opto-electronic confinement layer. Electronics Letters, 2008, 44, 905.	1.0	13
59	Control of spontaneous emission from InP single quantum dots in GaInP photonic crystal nanocavities. Applied Physics Letters, 2010, 97, 181104.	3.3	13
60	Ultrafast gain dynamics in InP quantum-dot optical amplifiers. Applied Physics Letters, 2010, 97, 211103.	3.3	13
61	Charge control in InP/(Ga,In)P single quantum dots embedded in Schottky diodes. Physical Review B, 2011, 84, .	3.2	13
62	The effect of strained confinement layers in InP self-assembled quantum dot material. Semiconductor Science and Technology, 2012, 27, 094008.	2.0	13
63	Tuning Nonlinear Mechanical Mode Coupling in GaAs Nanowires Using Cross-Section Morphology Control. Nano Letters, 2016, 16, 7414-7420.	9.1	13
64	Absorption coefficients in AlGaInP lattice-matched to GaAs. Solar Energy Materials and Solar Cells, 2017, 164, 28-31.	6.2	13
65	Temperature characterisation of spectroscopic InGaP X-ray photodiodes. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2018, 908, 277-284.	1.6	13
66	Electron-beam pumped laser structures based on MBE grown superlattices. Journal of Crystal Growth, 1996, 159, 609-612.	1.5	12
67	Gain saturation in InPâˆ•GaInP quantum-dot lasers. Applied Physics Letters, 2005, 86, 011111.	3.3	12
68	High performance InP-based quantum cascade distributed feedback lasers with deeply etched lateral gratings. Applied Physics Letters, 2006, 89, 201117.	3.3	12
69	Demonstration of air-guided quantum cascade lasers without top claddings. Optics Express, 2007, 15, 14861.	3.4	12
70	Effect of Growth Temperature on InP QD Lasers. IEEE Photonics Technology Letters, 2010, 22, 88-90.	2.5	12
71	InP quantum dot lasers with temperature insensitive operating wavelength. Applied Physics Letters, 2013, 103, .	3.3	12
72	Determination of absorption coefficients in AlInP lattice matched to GaAs. Journal Physics D: Applied Physics, 2015, 48, 405101.	2.8	12

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73	10-Gb/s All-Optical 2R Regeneration Using an MQW Fabryâ€“PÃ‰rot Saturable Absorber and a Nonlinear Fiber. IEEE Photonics Technology Letters, 2004, 16, 617-619.	2.5	11
74	Single-photon avalanche diode detectors for quantum key distribution. IET Optoelectronics, 2007, 1, 249-254.	3.3	11
75	Direct imaging of a laser mode via midinfrared near-field microscopy. Applied Physics Letters, 2007, 90, 201114.	3.3	11
76	Light-polarization-independent nuclear spin alignment in a quantum dot. Physical Review B, 2011, 83, .	3.2	11
77	Visible light communication using InGaN optical sources with AlInGaP nanomembrane down-converters. Optics Express, 2016, 24, 10020.	3.4	11
78	InGaP (GaInP) mesa p-i-n photodiodes for X-ray photon counting spectroscopy. Scientific Reports, 2017, 7, 10206.	3.3	11
79	1GHz clocked distribution of electrically generated entangled photon pairs. Optics Express, 2020, 28, 36838.	3.4	11
80	Electrically tunable multiquantum-well InGaAsP-InGaAsP microphotonic filter. IEEE Photonics Technology Letters, 2005, 17, 837-839.	2.5	10
81	Room-Temperature GaAs/AlGaAs Quantum Cascade Lasers Grown by Metalâ€“Organic Vapor Phase Epitaxy. IEEE Photonics Technology Letters, 2011, 23, 774-776.	2.5	10
82	High Repetition Rate Ti:Sapphire Laser Mode-Locked by InP Quantum-Dot Saturable Absorber. IEEE Photonics Technology Letters, 2011, 23, 1603-1605.	2.5	10
83	Exploring the wavelength range of InP/AlGaInP QDs and application to dual-state lasing. Semiconductor Science and Technology, 2015, 30, 044002.	2.0	10
84	Reducing Thermal Carrier Spreading in InP Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 668-673.	2.9	10
85	Temperature study of Al0.52In0.48P detector photon counting X-ray spectrometer. Journal of Applied Physics, 2016, 120, .	2.5	10
86	Investigation of a temperature tolerant InGaP (GaInP) converter layer for a63Ni betavoltaic cell. Journal Physics D: Applied Physics, 2017, 50, 345101.	2.8	10
87	ZnSe:Sb/ZnSe:Cl heteroepitaxial LED grown by MOVPE. Journal of Crystal Growth, 2000, 214-215, 1163-1165.	1.5	9
88	High-Speed 1.56-μm Multiple Quantum Well Asymmetric Fabry-Perot Modulator/Detector (AFPMD) for Radio-Over-Fibre Applications. , 2005, , .		9
89	Dot Density Effect by Quantity of Deposited Material in InP/AlGaInP Structures. IEEE Photonics Technology Letters, 2011, 23, 1169-1171.	2.5	9
90	Temperature dependence of avalanche multiplication and breakdown voltage in Al0.52In0.48P. Journal of Applied Physics, 2014, 115, .	2.5	9

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91	Temperature dependence of an AlInP63Ni betavoltaic cell. Journal of Applied Physics, 2016, 120, 144501.	2.5	9
92	Energy response characterization of InGaP X-ray detectors. Journal of Applied Physics, 2018, 124, 195704.	2.5	9
93	Electron Beam Pumped MQW InGaN/GaN Laser. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	8
94	ZnSe/ZnMgSSe QW Structures grown by MOVPE on ZnSe(1 0 0), ZnSe(5 1 1) and GaAs(1 0 0) substrates. Journal of Crystal Growth, 1998, 184-185, 124-128.	1.5	8
95	Temperature dependence of breakdown and avalanche multiplication in In/sub 0.53/Ga/sub 0.47/As diodes and heterojunction bipolar transistors. IEEE Transactions on Electron Devices, 2003, 50, 2021-2026.	3.0	8
96	Signal stability in periodically amplified fiber transmission systems using multiple quantum well saturable absorbers for regeneration. Journal of Lightwave Technology, 2006, 24, 747-754.	4.6	8
97	1W CW red VECSEL frequency-doubled to generate 60mW in the ultraviolet. , 2006, , .		8
98	Intersubband gain-induced dispersion. Optics Letters, 2009, 34, 208.	3.3	8
99	Passively Q-switched Pr:YLF laser. , 2011, , .		8
100	High-Gain InAs Planar Avalanche Photodiodes. Journal of Lightwave Technology, 2016, 34, 2639-2644.	4.6	8
101	Al0.6Ga0.4As x-ray avalanche photodiodes for spectroscopy. Semiconductor Science and Technology, 2020, 35, 095026.	2.0	8
102	Surface passivation of InP/InGaAs heterojunction bipolar transistors. Semiconductor Science and Technology, 2004, 19, 720-724.	2.0	7
103	Fabrication of novel quantum cascade lasers using focused ion beam (FIB) processing. Journal of Physics: Conference Series, 2006, 26, 215-218.	0.4	7
104	Proof-of-principle of surface detection with air-guided quantum cascade lasers. Optics Express, 2008, 16, 6387.	3.4	7
105	Room-Temperature Operation of Discrete-Mode InGaAsâ€“AlAsSb Quantum-Cascade Laser With Emission at $lambda=3.3 mu$m. IEEE Photonics Technology Letters, 2010, 22, 1273-1275.	2.5	7
106	Absorption, Gain, and Threshold in InP/AlGaInP Quantum Dot Laser Diodes. IEEE Journal of Quantum Electronics, 2013, 49, 389-394.	1.9	7
107	InAsP/AlGaInP/GaAs QD laser operating at â^¼770 nm. Journal of Physics: Conference Series, 2016, 740, 012008.	0.4	7
108	Transmission electron microscopy of AlGaAs/GaAs quantum cascade laser structures. Journal of Microscopy, 2017, 268, 298-304.	1.8	7

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109	Temperature effects on an InGaP (GaInP) 55Fe X-ray photovoltaic cell. Scientific Reports, 2017, 7, 4981.	3.3	7
110	High temperature AlInP X-ray spectrometers. Scientific Reports, 2019, 9, 12155.	3.3	7
111	Monolithic InP Quantum Dot Mode-Locked Lasers Emitting at 730 nm. IEEE Photonics Technology Letters, 2020, 32, 1073-1076.	2.5	7
112	Room temperature âˆ¼3.3â€…[micro sign]m InP-based InGaAs/AlAs(Sb) quantum cascade lasers. Electronics Letters, 2010, 46, 439.	1.0	6
113	AlInP X-ray photodiodes without incomplete charge collection noise. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2020, 960, 163606.	1.6	6
114	AlGaInP laser diodes incorporating a 3Î»â•4 multiple quantum barrier. Applied Physics Letters, 2005, 86, 021102.	3.3	5
115	Current injection tunable monolithically integrated InGaAs-InAlGaAs asymmetric Mach-Zehnder interferometer using quantum-well intermixing. IEEE Photonics Technology Letters, 2005, 17, 1677-1679.	2.5	5
116	Enhanced linear dynamic range of asymmetric Fabry-Pe/spl acute/rot modulator/detector. IEEE Photonics Technology Letters, 2006, 18, 770-772.	2.5	5
117	Optical Mode Control of Surface-Plasmon Quantum Cascade Lasers. IEEE Photonics Technology Letters, 2006, 18, 2499-2501.	2.5	5
118	GaInPâ•GaAs double heterojunction bipolar transistor with GaAsâ•Al0.11Ga0.89Asâ•GaInP composite collector. Journal of Applied Physics, 2006, 100, 026105.	2.5	5
119	Avalanche Noise in Al_{0.52}In_{0.48}P Diodes. IEEE Photonics Technology Letters, 2016, 28, 481-484.	2.5	5
120	X-ray spectroscopy with an AlInP photodiode. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 943, 162467.	1.6	5
121	Improved Planar InAs Avalanche Photodiodes With Reduced Dark Current and Increased Responsivity. Journal of Lightwave Technology, 2019, 37, 2375-2379.	4.6	5
122	Wide bandgap semiconductor conversion devices for radioisotope microbatteries. Materials Science in Semiconductor Processing, 2022, 142, 106533.	4.0	5
123	ZnSe/ZnMgSSe QW structures grown by MOVPE on transparent ZnSSe substrates. Microelectronic Engineering, 2000, 51-52, 19-26.	2.4	4
124	SCANNING E-BEAM LONGITUDINALLY PUMPED RT OPERABLE LASER BASED ON MOVPE-GROWN GaInP/AlGaInP MQW STRUCTURE. International Journal of Nanoscience, 2004, 03, 193-201.	0.7	4
125	Pulsed operation of long-wavelength (â‰ƒ11.3â€…[micro sign]m) MOVPE-grown quantum cascade lasers up to 350â€…K. Electronics Letters, 2005, 41, 1175.	1.0	4
126	Low threshold room temperature GaAs/AlGaAs quantum cascade laser with InAlP waveguide. Electronics Letters, 2011, 47, 1193.	1.0	4

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127	6Î¼m thick AlInP⁵⁵Fe x-ray photovoltaic and⁶³Ni betavoltaic cells. Semiconductor Science and Technology, 2018, 33, 105003.	2.0	4
128	A GaInAs/AlInAs quantum cascade laser with an emission wavelength of 5.6 Î¼m. Quantum Electronics, 2018, 48, 472-475.	1.0	4
129	ZnSe/ZnMgSSe structures on ZnSSe substrates. Journal of Crystal Growth, 2000, 214-215, 355-358.	1.5	3
130	Carrier distribution, spontaneous emission, and gain in self-assembled quantum dot lasers. , 2004, 5365, 86.		3
131	High current InP/InGaAs evanescently coupled waveguide phototransistor. IEE Proceedings: Optoelectronics, 2005, 152, 140.	0.8	3
132	Laser cathode-ray tube with a monolithic laser screen. Quantum Electronics, 2007, 37, 853-856.	1.0	3
133	Integrated Photonic Electromagnetic Band Gap Antenna with InGaAs/AlInGaAs Multiple Quantum Well Asymmetric Fabry-Perot Modulator. , 2007, , .		3
134	Intracavity near-field optical imaging of a mid-infrared quantum cascade laser mode. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 149, 270-274.	3.5	3
135	Higher catastrophic optical mirror damage power density level at facet from quantum dot material. , 2008, , .		3
136	STEM imaging of InP/AlGaInP quantum dots. Journal of Physics: Conference Series, 2010, 245, 012087.	0.4	3
137	Growth of low density InP/GaInP quantum dots. Journal of Physics: Conference Series, 2010, 245, 012061.	0.4	3
138	Î»â^¼3.36â€‚Î¼m room temperature InGaAs/AlAs(Sb) quantum cascade lasers with third order distributed feedback grating. Applied Physics Letters, 2010, 97, 111113.	3.3	3
139	Transmission Properties of Plasmonic Metamaterial Quantum Cascade Lasers. IEEE Photonics Technology Letters, 2010, 22, 1217-1219.	2.5	3
140	Origin of the temperature dependence of threshold current in InP/AlGaInP quantum dot lasers. , 2011, , .		3
141	Design of high sensitivity detector for underwater communication system. , 2013, , .		3
142	Twinning in GaAs nanowires on patterned GaAs(111)B. Crystal Research and Technology, 2015, 50, 62-68.	1.3	3
143	InGaP electron spectrometer for high temperature environments. Scientific Reports, 2019, 9, 11096.	3.3	3
144	AlInP photodiode x-ray detectors. Journal Physics D: Applied Physics, 2019, 52, 225101.	2.8	3

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145	GaAs/Al0.8Ga0.2As separate absorption and multiplication region x-ray spectroscopic avalanche photodiodes. Journal of Applied Physics, 2020, 128, .	2.5	3
146	Impact Ionization Coefficients in (Al_xGa_{1-x}) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 707 Td (</sub>)<su Lattice-Matched to GaAs. IEEE Transactions on Electron Devices, 2021, 68, 4045-4050.	3.0	3
147	Photo- and cathodoluminescence of ZnSSe quantum well heterostructures grown by MOVPE. Journal of Crystal Growth, 1996, 159, 518-522.	1.5	2
148	High-performance quantum cascade lasers grown by metal-organic vapor phase epitaxy. , 2004, , .		2
149	MOVPE grown quantum cascade lasers. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 863-866.	2.7	2
150	Enhanced linear dynamic range of asymmetric Fabry-Pe/spl acute/rot modulator/detector. IEEE Photonics Technology Letters, 2006, 18, 1040-1042.	2.5	2
151	IEEE 802.11a Data Over Fiber Transmission Using Electromagnetic Bandgap Photonic Antenna With Integrated Asymmetric Fabryâ€“PÃ‰rot Modulator/Detector. Journal of Lightwave Technology, 2008, 26, 2671-2678.	4.6	2
152	Effect of temperature on threshold current density in InP/AlGaInP quantum dot laser structures. International Journal of Nano and Biomaterials, 2009, 2, 147.	0.1	2
153	Higher power density limit at COMD in GaInP/AlGaInP in quantum dots than in wells. , 2009, , .		2
154	Optimization of low density InP/GaInP quantum dots for single-dot studies. Journal of Physics: Conference Series, 2010, 245, 012093.	0.4	2
155	High-Peak-Power Room-Temperature $lambdasim 3.6 mu$m InGaAsâ€“AlAs(Sb) Quantum Cascade Lasers. IEEE Photonics Technology Letters, 2010, 22, 757-759.	2.5	2
156	Recent progress in short wavelength quantum cascade lasers. , 2011, , .		2
157	High temperature â^¼4â€…[micro sign]m In0.7Ga0.3As/In0.34Al0.66As quantum cascade lasers grown by MOVPE. Electronics Letters, 2011, 47, 559.	1.0	2
158	Spectroscopic study of transparency current in mid-infrared quantum cascade lasers. Optics Express, 2012, 20, 18925.	3.4	2
159	Strained confinement layers in InP quantum dot lasers. , 2012, , .		2
160	InAs electron avalanche photodiodes with 580 GHz gain-bandwidth product. , 2012, , .		2
161	High sensitivity InAs photodiodes for mid-infrared detection. , 2016, , .		2
162	Quantum cascade laser with bound-to-quasi-continuum optical transitions at a temperature of up to 371 K. Quantum Electronics, 2020, 50, 710-713.	1.0	2

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163	The response of thick (10â€‰Î¼m) AlInP x-ray and Î³-ray detectors at up to 88â€‰keV. Journal of Applied Physics, 2021, 129, 243105.	2.5	2
164	InGaP 2 <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e1958" altimg="si70.svg"><mml:mo>Ã—</mml:mo></mml:math> 2 pixel array for X-ray and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e1963" altimg="si294.svg"><mml:mi>Î³</mml:mi></mml:math>-ray spectroscopy. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 1010, 165549.	1.6	2
165	Electron beam activation of acceptors in MOVPE ZnSe : N. Journal of Crystal Growth, 1998, 184-185, 435-439.	1.5	1
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